

Ordering number : EN8719



SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET
ECH8622R — General-Purpose Switching Device
 Applications

Features

- Low ON-resistance.
- Best suited for lithium battery applications.
- 2.5V drive.
- Composite type, facilitating high-density mounting.
- Drain common specifications.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		7	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² X0.8mm) 1unit	1.4	W
Total Dissipation	P _T	Mounted on a ceramic board (900mm ² X0.8mm)	1.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _D =30V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _D =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _D =10V, I _D =1mA	0.5		1.3	V
Forward Transfer Admittance	y _{fs}	V _D =10V, I _D =3.5A	6	10		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =4A, V _{GS} =4.5V	12.6	18	23	mΩ
	R _{DS(on)2}	I _D =4A, V _{GS} =4.0V	13.3	19	25	mΩ
	R _{DS(on)3}	I _D =4A, V _{GS} =3.1V	14.3	22	29	mΩ
	R _{DS(on)4}	I _D =2A, V _{GS} =2.5V	15	25	34	mΩ
Input Capacitance	C _{iss}	V _D =10V, f=1MHz		1220		pF
Output Capacitance	C _{oss}	V _D =10V, f=1MHz		180		pF
Reverse Transfer Capacitance	C _{rss}	V _D =10V, f=1MHz		140		pF

Marking : WG

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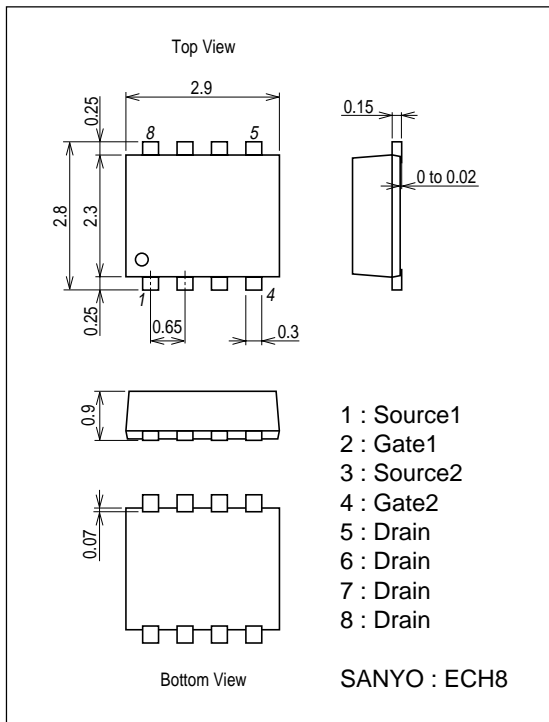
ECH8622R

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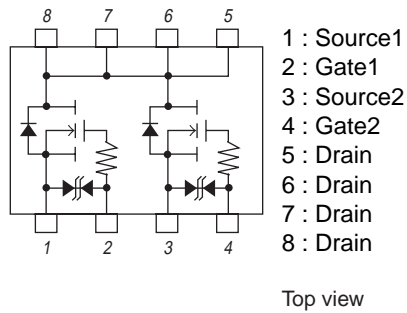
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_d(\text{on})$	See specified Test Circuit.		585		ns
Rise Time	t_r	See specified Test Circuit.		1680		ns
Turn-OFF Delay Time	$t_d(\text{off})$	See specified Test Circuit.		4960		ns
Fall Time	t_f	See specified Test Circuit.		2660		ns
Total Gate Charge	Qg	$V_{DS}=10V, V_{GS}=4.5V, I_D=7A$		14		nC
Gate-to-Source Charge	Qgs	$V_{DS}=10V, V_{GS}=4.5V, I_D=7A$		2		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=10V, V_{GS}=4.5V, I_D=7A$		4.3		nC
Diode Forward Voltage	V_{SD}	$I_S=7A, V_{GS}=0V$		0.84	1.2	V

Package Dimensions

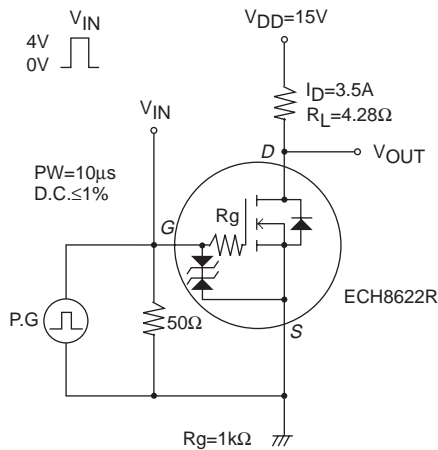
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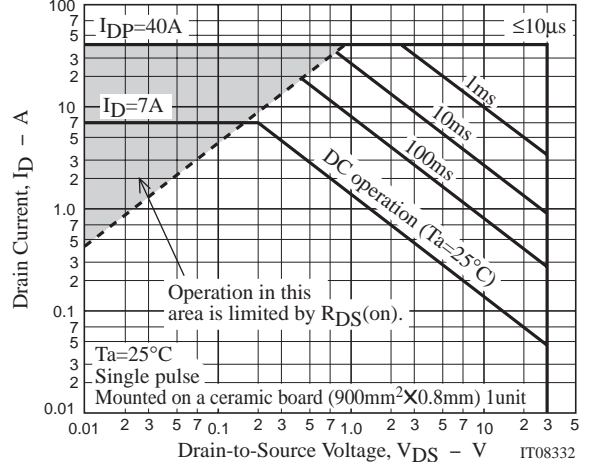
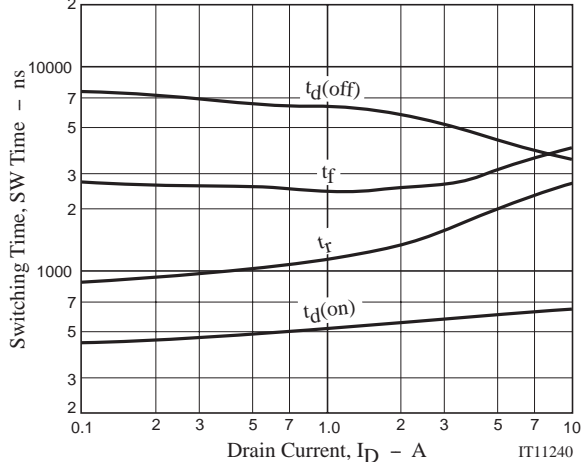
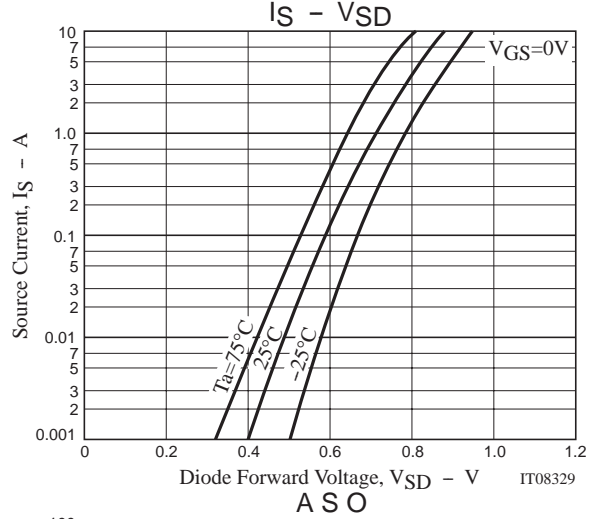
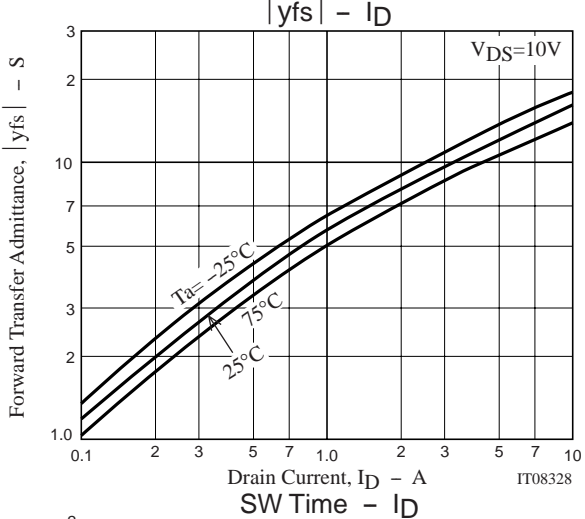
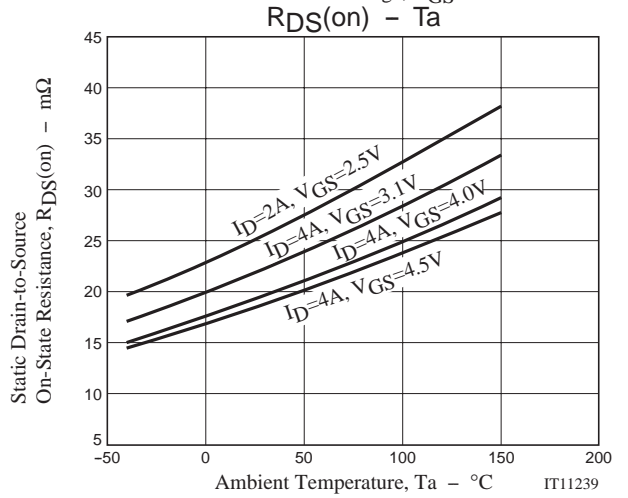
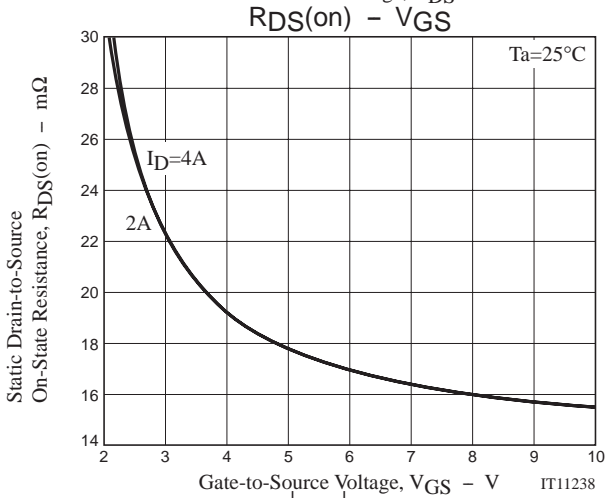
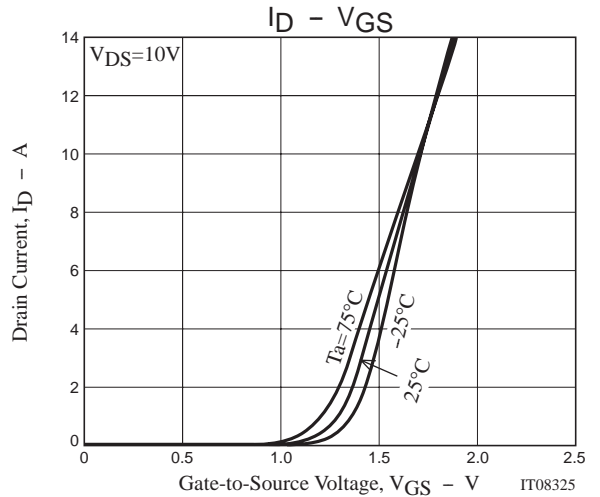
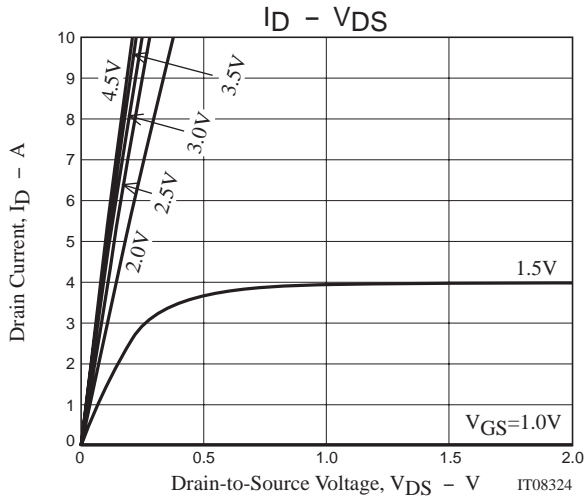
Electrical Connection



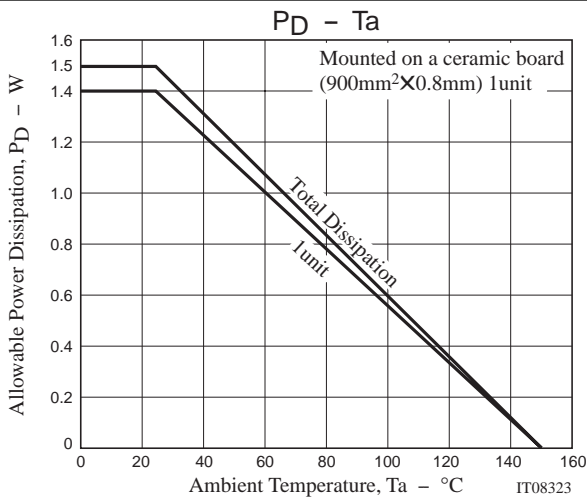
Switching Time Test Circuit



ECH8622R



ECH8622R



Note on usage : Since the ECH8622R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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